

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
 Shunpei YAMAZAKI et al.)
 Serial No. 09/362,192)
 Filed: July 28, 1999)
 For: SEMICONDUCTOR DEVICE)
 HAVING SEMICONDUCTOR)
 CIRCUIT COMPRISING)
 SEMICONDUCTOR ELEMENT)
 AND METHOD FOR)
 MANUFACTURING THE SAME)

Group Art Unit: 2812

Examiner: V. Simkovic

Attorney Docket No. 740756-2011



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 V. Vannad

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AMENDMENT

Honorable Commissioner for Patents
 Washington, D.C. 20231
 Sir:

In response to the Office Action dated April 30, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 45-50, 52-54 and 56-66 and add new claims 67-72 as follows:

45. (Amended) A method for manufacturing a semiconductor device comprising steps of:

contacting a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma, thereby a gate insulating film formed on said semiconductor film; and

crystallizing said semiconductor film to obtain a crystalline semiconductor film.

46. (Amended) A method according to claim 45, wherein said crystallizing is performed by crystallizing said semiconductor film by irradiating with an infrared ray or a laser light.

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